

Silicon Carbide Schottky Diode		REVERSE VOLTAGE 650 Volts FORWARD CURRENT 8 Amperes																																																																														
FEATURES <ul style="list-style-type: none"> • No reverse recovery/No forward recovery • 650-volts Schottky Rectifier • High Frequency Operation • Temperature independent switching behavior • Extremely Fast Switching • Positive Temperature Coefficient on VF 		TO-220AC  																																																																														
MECHANICAL DATA <ul style="list-style-type: none"> • Case: TO-220AC • Polarity: Cathode Band 																																																																																
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS <p>Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%</p>																																																																																
<table border="1"> <thead> <tr> <th>Characteristics</th> <th>Symbol</th> <th colspan="2">SiC0865ST</th> <th>Unit</th> </tr> </thead> <tbody> <tr> <td>Maximum Repetitive Peak Reverse Voltage</td> <td>V_{RRM}</td> <td colspan="2">650</td> <td>V</td> </tr> <tr> <td>RMS Reverse Voltage</td> <td>V_{RMS}</td> <td colspan="2">650</td> <td>V</td> </tr> <tr> <td>Maximum DC blocking voltage</td> <td>V_{DC}</td> <td colspan="2">650</td> <td>V</td> </tr> <tr> <td>Diode Forward Voltage $I_F=6A$</td> <td rowspan="2">V_F</td> <td>Typ.</td> <td>Max.</td> <td rowspan="2">V</td> </tr> <tr> <td>$T_J=25^\circ C$ $T_J=175^\circ C$</td> <td>1.47 1.75</td> <td>1.8 2.5</td> </tr> <tr> <td>Reverse Current $V_R=650V$</td> <td>I_R</td> <td>10 15</td> <td>100 200</td> <td>μA</td> </tr> <tr> <td>Continuous forward current</td> <td>I_F</td> <td></td> <td>25 11 8</td> <td>A</td> </tr> <tr> <td>Surge non-repetitive forward current $TC=25^\circ C, tp=10ms$, Half Sine-wave</td> <td>I_{FSM}</td> <td></td> <td>56</td> <td>A</td> </tr> <tr> <td>Diode dv/dt ruggedness $V_R=0...480V$</td> <td>dv/dt</td> <td></td> <td>100</td> <td>V/ns</td> </tr> <tr> <td>Total capacitive charge $V_R=650V$, $di/dt=500A/\mu s, I_F=6A, T_J=25^\circ C$</td> <td>$Q_C$</td> <td>23</td> <td></td> <td>nC</td> </tr> <tr> <td>Total Capacitance $T_J=25^\circ C, f=1MHz$</td> <td rowspan="3">C</td> <td>$V_R=0V$</td> <td>550</td> <td rowspan="3">pF</td> </tr> <tr> <td>$V_R=200V$</td> <td>55</td> </tr> <tr> <td>$V_R=400V$</td> <td>53</td> </tr> <tr> <td>Power dissipation</td> <td>P_{tot}</td> <td>102 45</td> <td></td> <td>W</td> </tr> <tr> <td>Thermal Resistance, Junction Case</td> <td>R_{thJC}</td> <td colspan="2">1.46</td> <td>°C/W</td> </tr> <tr> <td>Junction and Storage Temperature Range</td> <td>T_J, T_{STG}</td> <td colspan="2">-55 to +175</td> <td>°C</td> </tr> </tbody> </table>				Characteristics	Symbol	SiC0865ST		Unit	Maximum Repetitive Peak Reverse Voltage	V_{RRM}	650		V	RMS Reverse Voltage	V_{RMS}	650		V	Maximum DC blocking voltage	V_{DC}	650		V	Diode Forward Voltage $I_F=6A$	V_F	Typ.	Max.	V	$T_J=25^\circ C$ $T_J=175^\circ C$	1.47 1.75	1.8 2.5	Reverse Current $V_R=650V$	I_R	10 15	100 200	μA	Continuous forward current	I_F		25 11 8	A	Surge non-repetitive forward current $TC=25^\circ C, tp=10ms$, Half Sine-wave	I_{FSM}		56	A	Diode dv/dt ruggedness $V_R=0...480V$	dv/dt		100	V/ns	Total capacitive charge $V_R=650V$, $di/dt=500A/\mu s, I_F=6A, T_J=25^\circ C$	Q_C	23		nC	Total Capacitance $T_J=25^\circ C, f=1MHz$	C	$V_R=0V$	550	pF	$V_R=200V$	55	$V_R=400V$	53	Power dissipation	P_{tot}	102 45		W	Thermal Resistance, Junction Case	R_{thJC}	1.46		°C/W	Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +175		°C
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Application <ul style="list-style-type: none"> • Switch mode power supply • Power factor correction • Solar inverter • Uninterruptible power supply • High Efficiency DC/DC Converters • Motor Drivers 																																																																																

Rating and Characteristic Curves

Fig 1.Typical forward characteristics

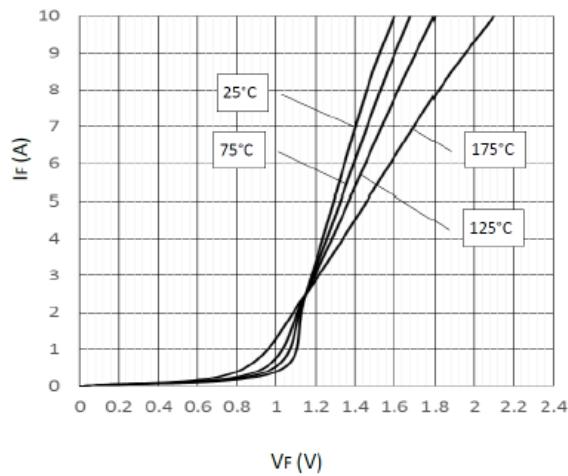


Fig 2.Diode forward current

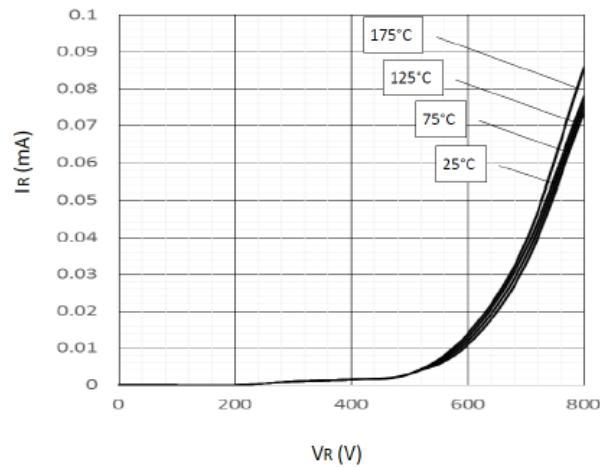


Fig 3.Current Derating

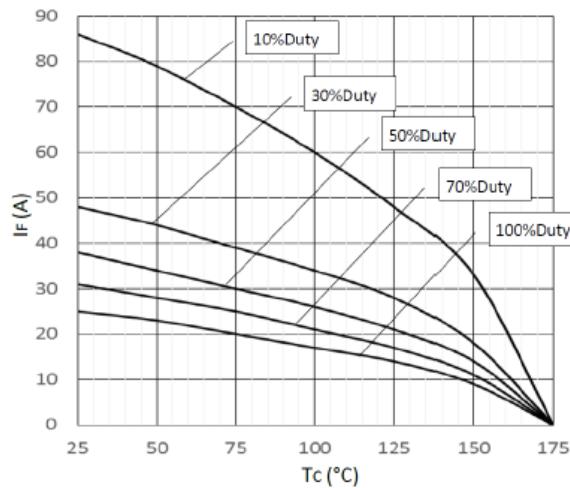
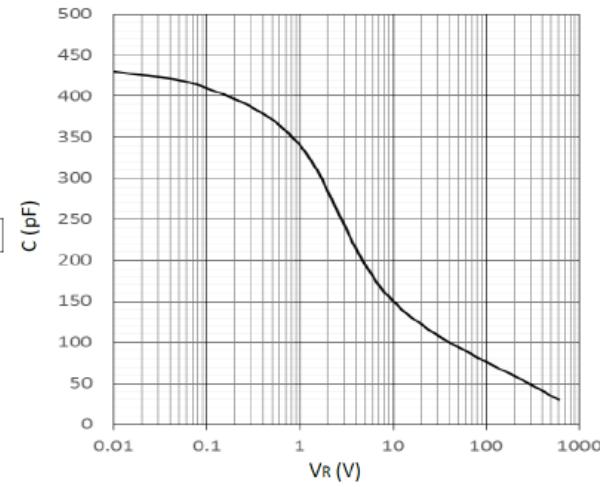
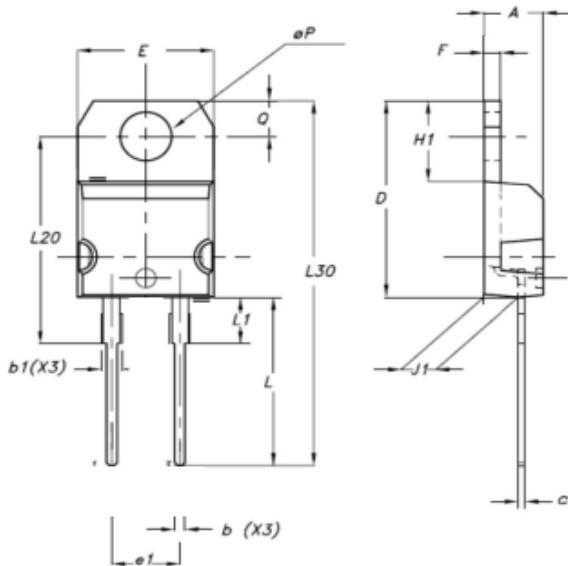


Fig 4.Typical capacitance vs. reverse voltage



Package outline



DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
eP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

TO-220 Tube outline

